

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 1800 \text{ V}$$

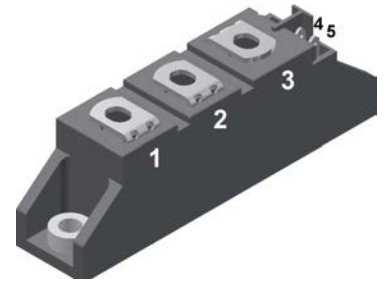
$$I_{TAV} = 110 \text{ A}$$

$$V_T = 1,21 \text{ V}$$


Phase leg

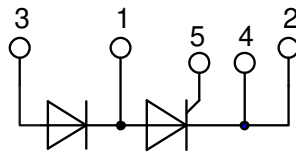
Part number

MCMA110PD1800TB



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

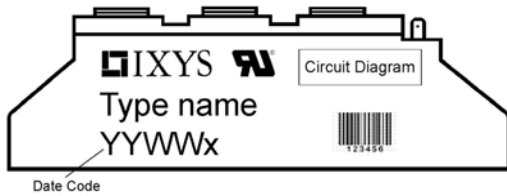
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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1800	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1800 V$	$T_{VJ} = 25^{\circ}C$		100	μA
		$V_{R/D} = 1800 V$	$T_{VJ} = 140^{\circ}C$		10	mA
V_T	forward voltage drop	$I_T = 110 A$	$T_{VJ} = 25^{\circ}C$		1,24	V
		$I_T = 220 A$			1,52	V
		$I_T = 110 A$	$T_{VJ} = 125^{\circ}C$		1,21	V
		$I_T = 220 A$			1,57	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		110	A
$I_{T(RMS)}$	RMS forward current	180° sine			170	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0,85	V
r_T	slope resistance				3,3	m Ω
R_{thJC}	thermal resistance junction to case				0,3	K/W
R_{thCH}	thermal resistance case to heatsink			0,2		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		380	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		1,90	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		2,05	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		1,62	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1,75	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		18,1	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		17,5	kA ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		13,0	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		12,7	kA ² s
C_J	junction capacitance	$V_R = 400V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		95	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
P_{GAV}	average gate power dissipation				0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 330 A$			150	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0,45 \text{ A}/\mu s;$ $I_G = 0,45A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 110 A$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 140^{\circ}C$		1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1,5	V
			$T_{VJ} = -40^{\circ}C$		1,6	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		150	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0,2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		200	mA
		$I_G = 0,45A; di_G/dt = 0,45 \text{ A}/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0,45A; di_G/dt = 0,45 \text{ A}/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 110A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 \text{ A}/\mu s; dv/dt = 20 \text{ V}/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		185	μs



Package TO-240AA				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight					81	g
M_D	mounting torque		2,5		4	Nm
M_T	terminal torque		2,5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13,0	9,7		mm
$d_{Spb/Apb}$		terminal to backside	16,0	16,0		mm
V_{ISOL}	isolation voltage	t = 1 second		4800		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V



Part description

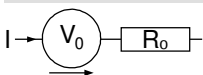
- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 110 = Current Rating [A]
- PD = Phase leg
- 1800 = Reverse Voltage [V]
- TB = TO-240AA-1B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA110PD1800TB	MCMA110PD1800TB	Box	36	

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}C$

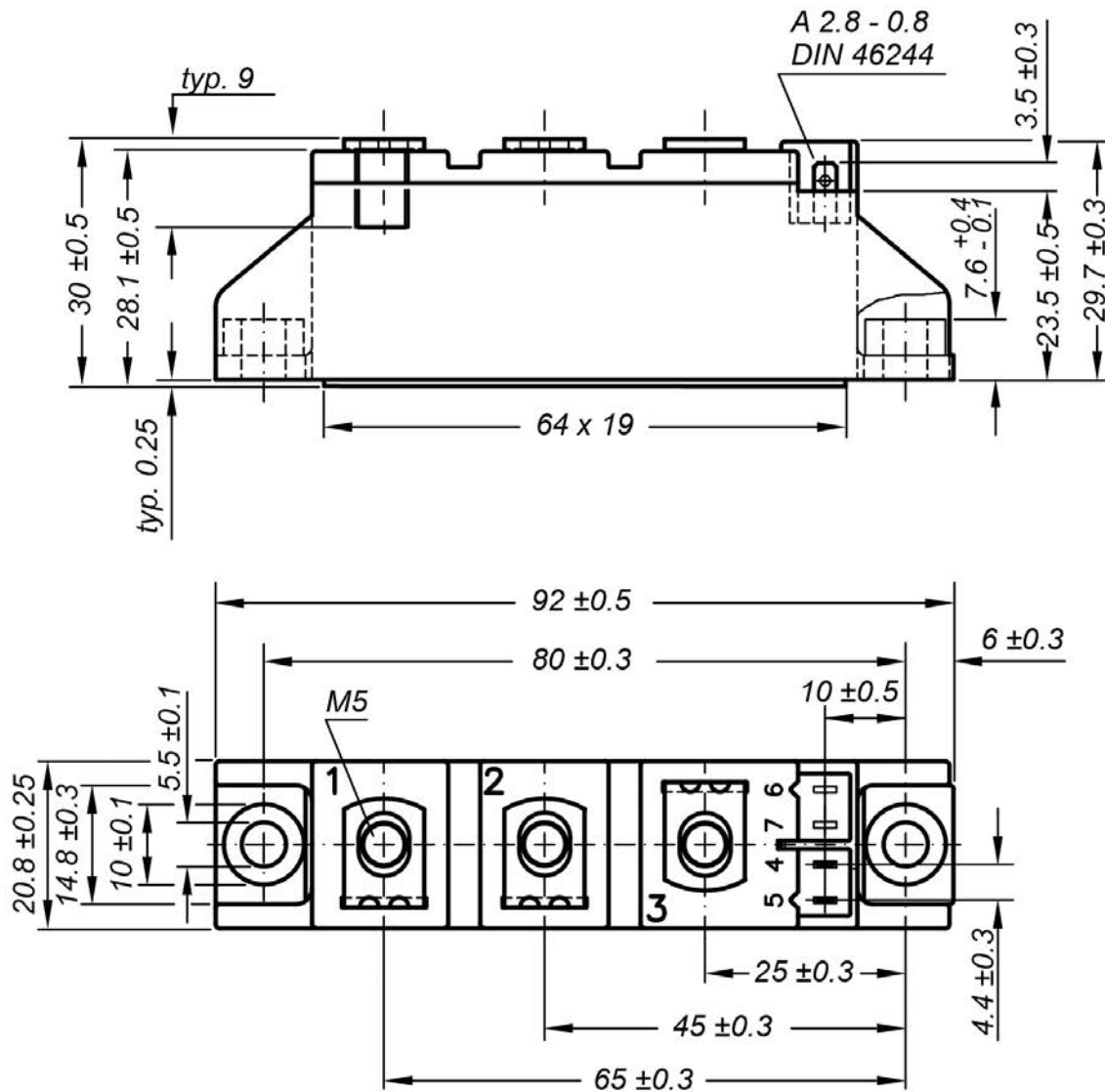


Thyristor

$V_{0\ max}$	threshold voltage	0,85	V
$R_{0\ max}$	slope resistance *	2,1	mΩ

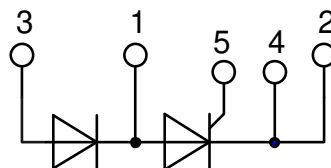


Outlines TO-240AA



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
Type ZY 200L (L = Left for pin pair 4/5) UL 758, style 3751



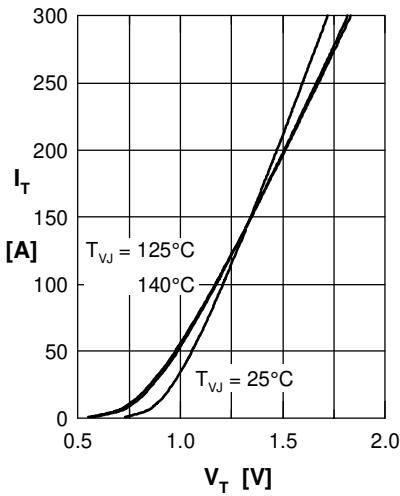
Thyristor


Fig. 1 Forward characteristics

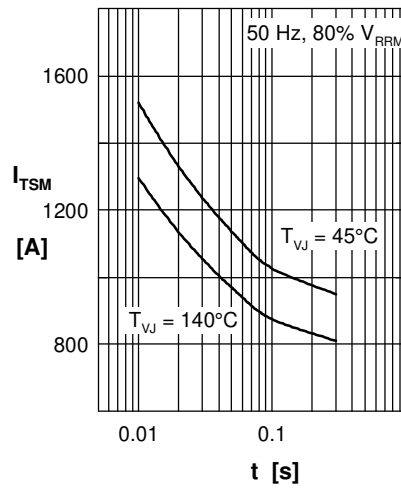
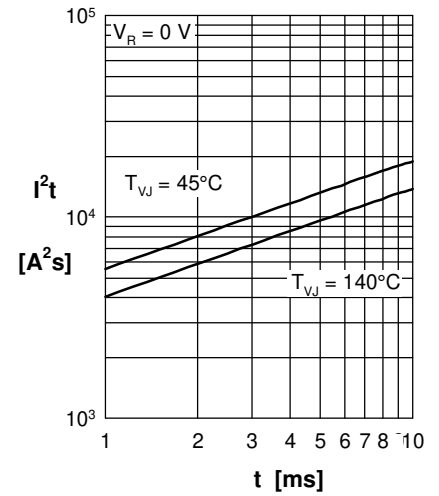
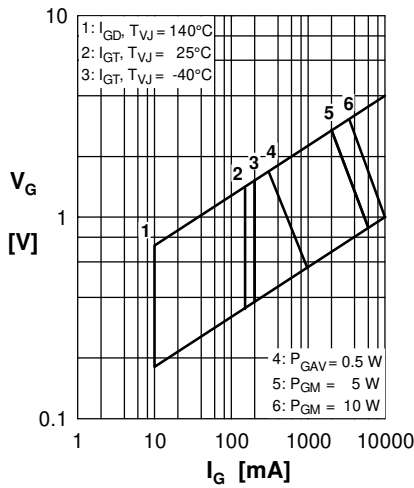

 Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 s)


Fig. 4 Gate voltage & gate current

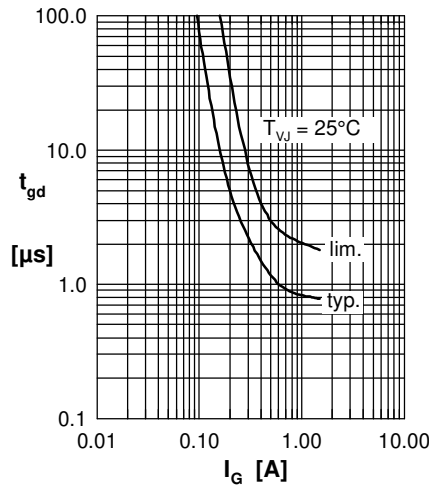
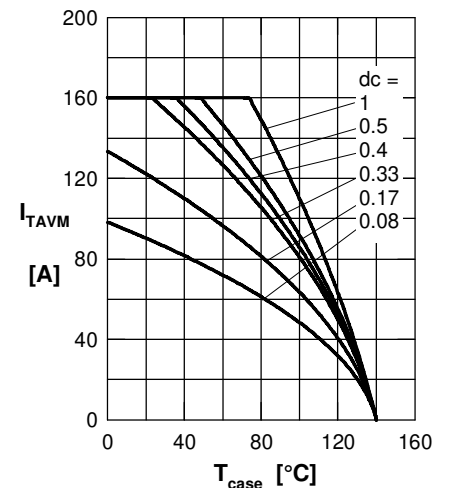

 Fig. 5 Gate controlled delay time t_{gd}


Fig. 6 Max. forward current at case temperature

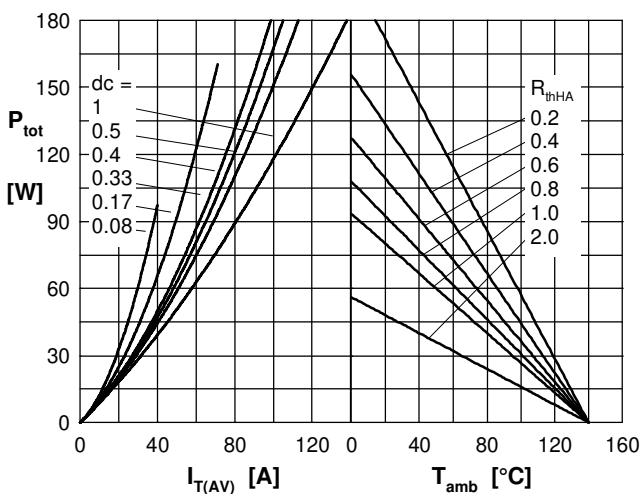
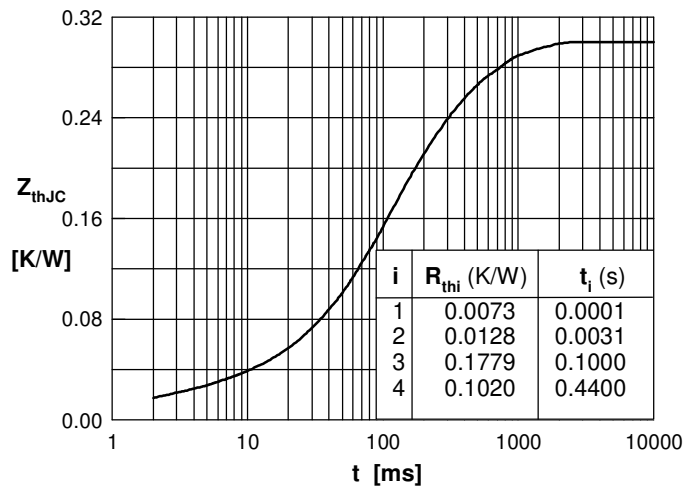

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case